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Refinement of the phase diagram of the MnSe–In₂Se₃ system and the crystal structures of MnIn₂Se₄ and Mn₂In₂Se₅ compounds

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Abstract

Complex chalcogenides based on transition elements, in particular ternary compounds of the AB₂X₄ type (M = Mn, Fe, Co, Ni; B = Ga, In, Sb, Bi; X = S, Se, Te) are among the important functional materials. Compounds of this class exhibit the phenomena of electronically or optically controlled magnetism and are very promising for the creation of lasers, light modulators, photodetectors, and other functional devices controlled by a magnetic field. Recent studies demonstrated that these compounds can also find application in photocatalysis, photovoltaics, and thermoelectric converters.

The study presents new data on phase equilibria in the MnSe–In₂Se₃ system, obtained by differential thermal analysis, X-ray phase analysis, and scanning electron microscopy. Two ternary compounds, MnIn₂Se₄ with congruent melting at 1193 K and Mn₂In₂Se₅, melting incongruently at 1196 K, were formed in the system. The first is a phase of variable composition and has a 5–6 mol. % homogeneity region towards an excess of In₂Se₃. Based on powder diffraction data, the Rietveld method was used to refine the crystal structures and lattice parameters of both ternary compounds.

Keywords: Manganese-indium selenides, Phase equilibria, Homogeneity region, Crystal structure, Rietveld method

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1. Introduction

Complex transition metal chalcogenides, in particular compounds of the AB₂X₄ and A₂B₂X₅ types (A = Fe, Mn, Co; B = Al, Ga, In, Sb, Bi; X = S, Se, Te) with a layered structure are among the important materials possessing thermoelectric [1, 2], magnetic [3–9], optical, and other functional properties [10–13]. This makes them very promising for use in the creation of lasers, light modulators, photodetectors, thermoelectric, and other functional devices. In addition, they are objects of intensive research as magnetic topological insulators, combining the properties of an antiferromagnet and a topological insulator, and are extremely promising for use in spintronics, quantum computing, and information processing devices [14–22].

A number of recent studies have shown that some compounds of the AB₂X₄ type and heterojunctions based on them can find application in photocatalysis and photovoltaics, in particular, in photocatalytic water splitting [23–27]. According to the results of [28–30], some compounds of the above type with a spinel structure are good candidates for use as a new type of anode materials for the stable storage of ions in lithium (sodium) ion batteries.

The results described above show the relevance of research aimed at obtaining and studying the properties of new complex layered chalcogenides of transition elements. Modification of such compounds by alloying and obtaining solid solutions can be used to optimize their functional properties [31–36].

The development of methods for the targeted synthesis of complex chalcogenide compounds and phases of variable composition is based on data of phase equilibria in the corresponding

systems. Phase diagrams provide valuable information on the nature of formation, thermal stability, phase transformations, primary crystallization regions, and the homogeneity of intermediate phases [37–43].

Previously, studies of phase equilibria in a number of quasi-ternary MX–Ga₂X₃–In₂X₃ systems (M = Mn, Fe; X = S, Se, Te) were performed, in search of the physicochemical foundations for creating new magnetic semiconductors [44–50]. In the indicated systems, new phases of variable composition based on ternary AB₂X₄ compounds have been identified, their primary crystallization fields and homogeneity regions were determined.

Preliminary experimental results in the study of the MnSe–Ga₂Se₃–In₂Se₃ system, revealed their discrepancy with the known [51] phase diagram of the MnSe–In₂Se₃ boundary system. Taking this into account these findings, in this study we have undertaken a repeated study of phase equilibria in the MnSe–In₂Se₃ system.

The initial compounds of the studied system were investigated in detail. The MnSe compound melts congruently at 1875 K and has three modifications: a stable low-temperature α -MnSe crystallizes in a cubic NaCl-type structure. The β -MnSe and γ -MnSe phases are unstable. The first phase crystallizes in a cubic structure of the sphalerite type, and the second crystallizes in a hexagonal structure of the wurtzite type [52–55], (Table 1).

The In₂Se₃ compound melts with an open maximum at 1158 K and undergoes three polymorphic transformations (473, 920, and 1023 K) [52, 53]. The types and parameters of crystal lattices of all four crystalline modifications of In₂Se₃ are described in detail in [56], (Table 1).

Table 1. Crystallographic data of MnSe and In₂Se₃

Соединение	Type and parameters of the crystal lattice, nm	Ref.
MnSe-rt	Kubik, Sp.Gr. $Fm\bar{3}m$; $a = 0.5456$	[54]
MnSe-ht1	Kubik, Sp.Gr. $F\bar{4}3m$; $a = 0.583$	[55]
MnSe-ht2	Heksaqonal, Sp.Gr. $P63mc$; $a = 0.413$, $c = 0.673$	[55]
In ₂ Se ₃ -rt	Heksaqonal, Sp.Gr. $R\bar{3}m$; $a = 0.405$, $c = 2.877$	[56]
In ₂ Se ₃ -ht1	Heksaqonal, Sp.Gr. $P6_3$; $a = 0.711$, $c = 1.930$	[56]
In ₂ Se ₃ -ht2	Heksaqonal, Sp.Gr. $P6_1$; $a = 0.7133$, $c = 1.934$	[56]
In ₂ Se ₃ -ht3	Heksaqonal, Sp.Gr. $P6_1$; $a = 0.4014$, $c = 0.964$	[56]

2. Experimental

2.1. Synthesis

The MnSe and In₂Se₃ compounds were synthesized by the direct interaction of stoichiometric quantities of high-purity elemental components (manganese – 99.95%, indium – 99.999% and selenium – 99.99% from Alfa Aesar) in sealed quartz glass ampoules evacuated to ~ 10⁻² Pa. The syntheses were carried out in a two-zone inclined furnace. The lower “hot” zone was heated to 1200 K, and the upper “cold” zone was heated to 900 K, which is slightly lower than the boiling point (958 K) of elemental selenium [57]. In order to avoid the interaction of quartz with manganese, MnSe synthesis was carried out in a graphitized ampoule.

The individuality of the synthesized compounds was controlled by differential thermal analysis (DTA) and X-ray diffraction (XRD) methods. Temperatures of polymorphic transitions and melting of In₂Se₃, determined based on the DTA heating curves, coincided with the available literature data [52, 53]. The following crystallographic parameters were obtained by interpretation of the powder X-ray diffraction patterns: MnSe – cubic, sp. gr. *Fm $\bar{3}$ m*, *a* = 0.54542(4) nm, RT-In₂Se₃ – hexagonal, sp. gr. *R $\bar{3}$ m*, *a* = 0.40804(5), *c* = 2.8712(14) nm, which are in good agreement with the literature data [54–56], (Table 1).

Alloys of the MnSe–In₂Se₃ system were prepared by fusing the initial binary compounds in various ratios in evacuated quartz ampoules at 1200–1300 K, followed by thermal annealing at 800 K for 500 hours and cooling in a switched-off furnace.

2.2. Research methods

The studies were carried out using DTA, X-ray diffraction and scanning electron microscopy (SEM) methods. The DTA of samples weighing 0.1–0.3 g in evacuated quartz ampoules was carried out using a Netzsch STA 449 F3 unit (platinum – platinum/rhodium thermocouples) in the temperature range from room temperature to ~ 1450 K with a heating rate of 10 K·min⁻¹. The temperature measurement accuracy was within ±2 K.

The X-ray powder diffraction analysis of powder samples was performed using a D2 Phaser diffractometer (Bruker, Germany; CuK α -radiation, angle range 5° ≤ 2θ ≤ 80°, scanning rate of

0.03°×0.2 min). The crystal lattice parameters of ternary compounds were refined by the Rietveld method using the EVA and TOPAS 4.2 programs. The SEM analysis was performed using the Tescan Vega 3 SBH scanning electron microscope.

3. Results and discussion

The joint processing of DTA, X-ray diffraction, and SEM data for synthesized and annealed alloys allowed us to obtain a new, more precise pattern of phase equilibria in the MnSe – In₂Se₃ system. Below in the text, in the figures and in the tables the following phase designations are used: α and γ-solid solutions based on the MnSe and MnIn₂Se₄; β₁, β₂, β₃ and β₄-solid solutions based on high-temperature, two intermediate and low-temperature modifications of the In₂Se₃ compound, respectively.

The X-ray diffraction method showed that alloys of composition 33.3 (Mn₂In₂Se₅) and 50 mol. % In₂Se₃ (MnIn₂Se₄) have individual diffraction patterns that differ from those of the original compounds. Diffraction patterns of other intermediate alloys consisted of two-phase mixtures α + Mn₂In₂Se₅, Mn₂In₂Se₅ + MnIn₂Se₄ (γ) and γ + β₄ respectively (Fig. 1).

Based on powder diffraction patterns, the Rietveld method was used to refine the crystal structures of both ternary compounds. The experimental and calculated diffraction patterns, as well as the differences in their intensities are shown in Fig. 2 and 3. The refined parameters of the elementary cells are shown in Table 2, and the atomic positional parameters are shown in Tables 3 and 4. The crystal structures of the MnIn₂Se₄ and Mn₂In₂Se₅ compounds are shown in Fig. 4. Both compounds are layered phases of the van der Waals type. Their structural blocks are fragments consisting of 7 and 9 atomic layers, in which the atoms alternate as Se-In-Se-Mn-Se-In-Se and Se-In-Se-Mn-Se-Mn-Se-In-Se respectively. In both structures, Mn atoms are located at the centers of octahedra, and In atoms are located at the centers of tetrahedra formed by Se atoms. These blocks are bound together by van der Waals bonds. The results obtained for polycrystalline samples using the Rietveld method are in good agreement with the data of studies [58, 59], obtained based on diffraction data of single crystals.

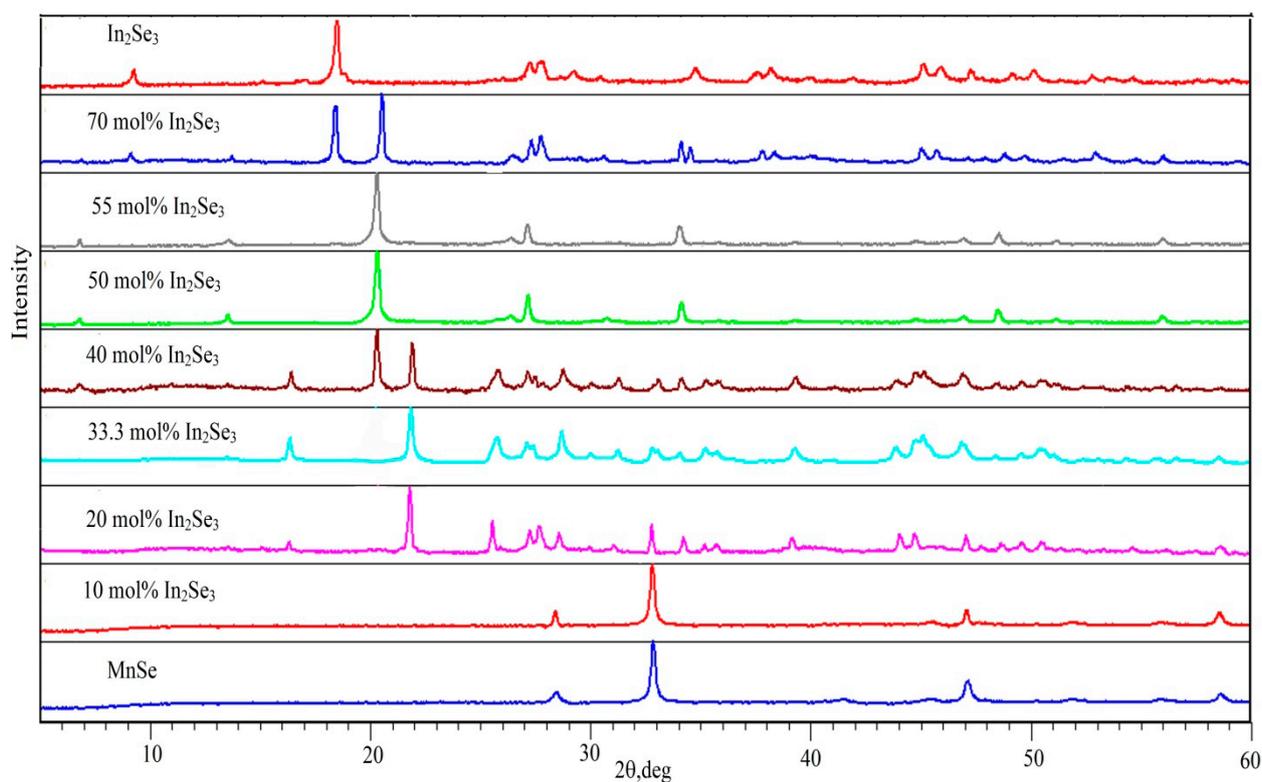


Fig. 1. The XRD patterns of alloys of the MnSe–In₂Se₃ system

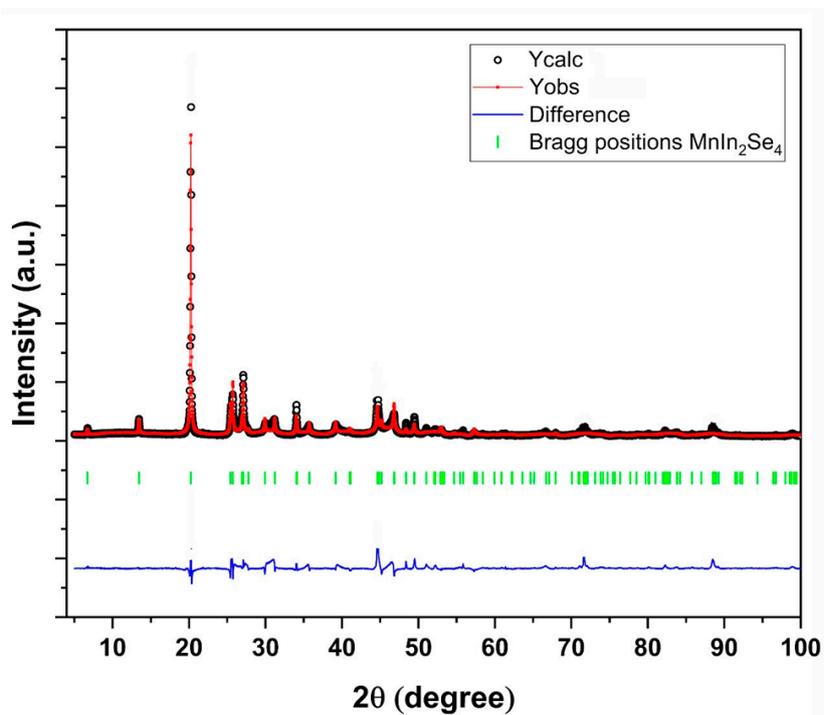


Fig. 2. Experimental and calculated diffraction lines of MnIn₂Se₄, as well as the differences in their intensities

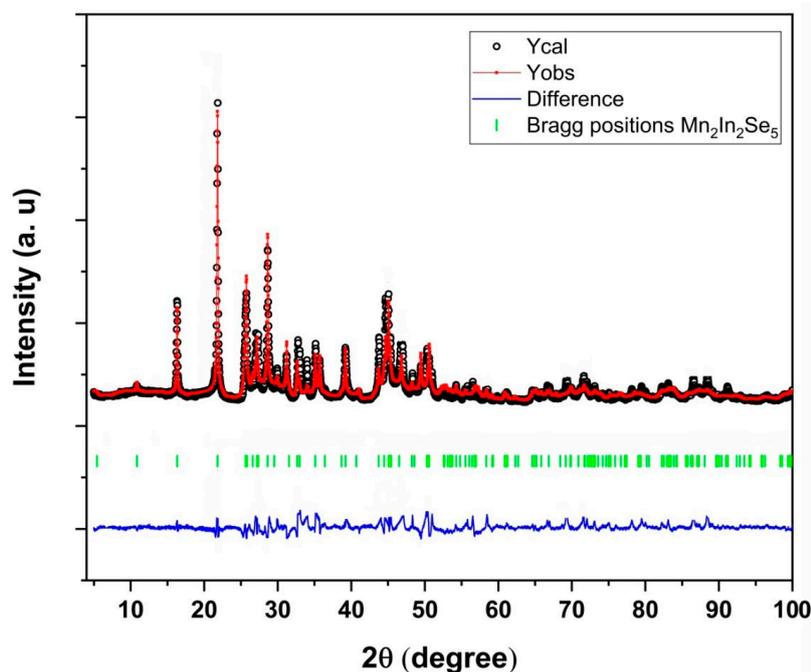


Fig. 3. Experimental and calculated diffraction lines of Mn₂In₂Se₅, as well as the differences in their intensities

Table. 2. Refined parameters of the structure of MnIn₂Se₄ and Mn₂In₂Se₅

Structure parameters	MnIn ₂ Se ₄	Mn ₂ In ₂ Se ₅
Space group	<i>R</i> $\bar{3}m$	<i>R</i> $\bar{3}m$
Cell parameters:		
<i>a</i> (nm)	0.405289(45)	0.402240(57)
<i>c</i> (nm)	3.94594(44)	4.87486(79)
The cell volume (nm ³)	0.56243(17)	0.68307(22)
Density (g/cm ³)	5.318(91)	5.36014(50)
R-Bragg (%)	0.873	0.428

Table. 3. Atomic positional parameters in MnIn₂Se₄

Atoms	Multiplicity of positions	<i>x</i>	<i>y</i>	<i>z</i>	Atom type	Relative occupation
In1	6	0.00000	0.00000	0.76964(31)	In ⁺³	1.000(42)
Se2	6	0.00000	0.00000	0.70467(46)	Se	1
Se1	6	0.00000	0.00000	0.12160(56)	Se	1
Mn	3	0.00000	0.00000	0.00000	Mn ⁺²	1.001(68)

Table.4. Atomic positional parameters in Mn₂In₂Se₅

Atoms	Multiplicity of positions	<i>x</i>	<i>y</i>	<i>z</i>	Atom type	Relative occupation
Se2	6	0.00000	0.00000	0.39354(22)	Se	1
Mn1	6	0.00000	0.00000	0.70092(31)	Mn ⁺²	1
Se1	6	0.00000	0.00000	0.13546(20)	Se	1
In2	6	0.00000	0.00000	0.55513(13)	In ⁺³	1
Se3	3	0.00000	0.00000	0.00000	Se	1

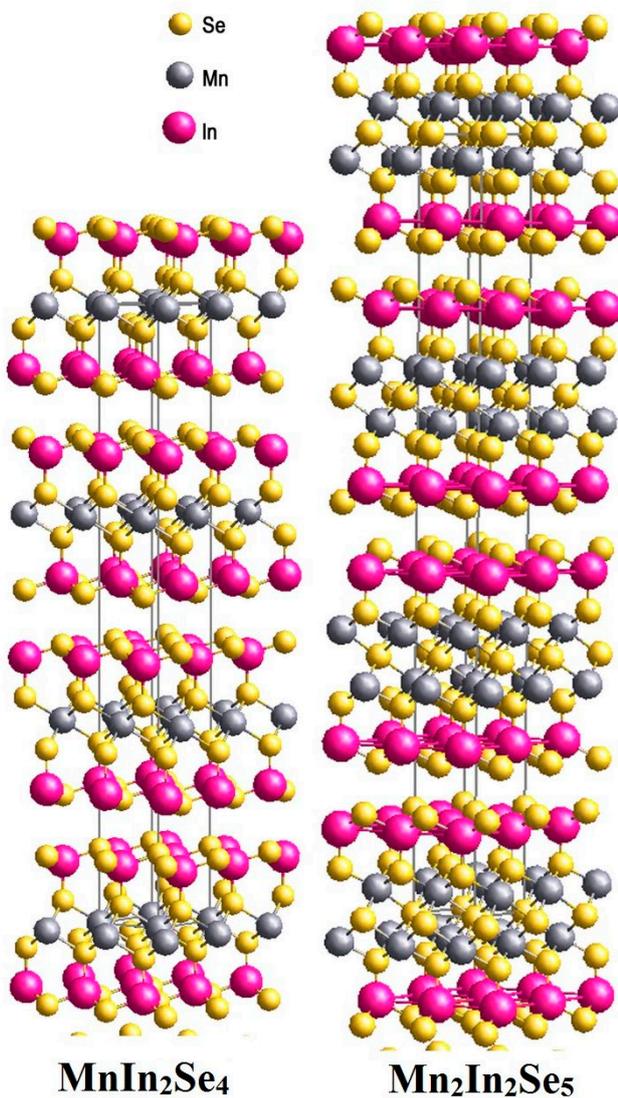


Fig. 4. Three-dimensional view of the structures of MnIn₂Se₄ and Mn₂In₂Se₅

It should be noted that the MgIn₂Se₄ and ZnIn₂Se₄ compounds are also characterized by a similar structure, however, the authors [60] chose an asymmetric space group $R\bar{3}m$ to describe the structure of MgIn₂Se₄.

Interpretation of DTA data on the heating of annealed alloys of MnSe–In₂Se₃ system (Table 5), taking into account the above presented XRD results, allowed us to construct a T - X phase diagram (Fig. 5). According to our data, the MnSe–In₂Se₃ system can be considered quasi-binary, since the compositions of all phases in equilibrium are on its T - X planes. The system is characterized by the formation of two intermediate compounds: the MnIn₂Se₄ compound melts congruently at 1195 K and has a wide homogeneity region

Table 5. DTA results of alloys of the MnSe–In₂Se₃ system

Composition, mol. % In ₂ Se ₃	Thermal effects, K
10	–
20	1195
30	1197; 1197–1440
33.3	1196; 1196–1390
35	1188–1196; 1196–1360
40	1188–1196; 1196–1285
45	1188
50	1195
55	1180–1193
60	1150–1190
70	462; 1148; 1148–1185
80	460; 1148; 1148–1176
90	463; 910; 1005; 1150
95	465; 910; 1005; 1148–1155
100	475; 920; 1023; 1163

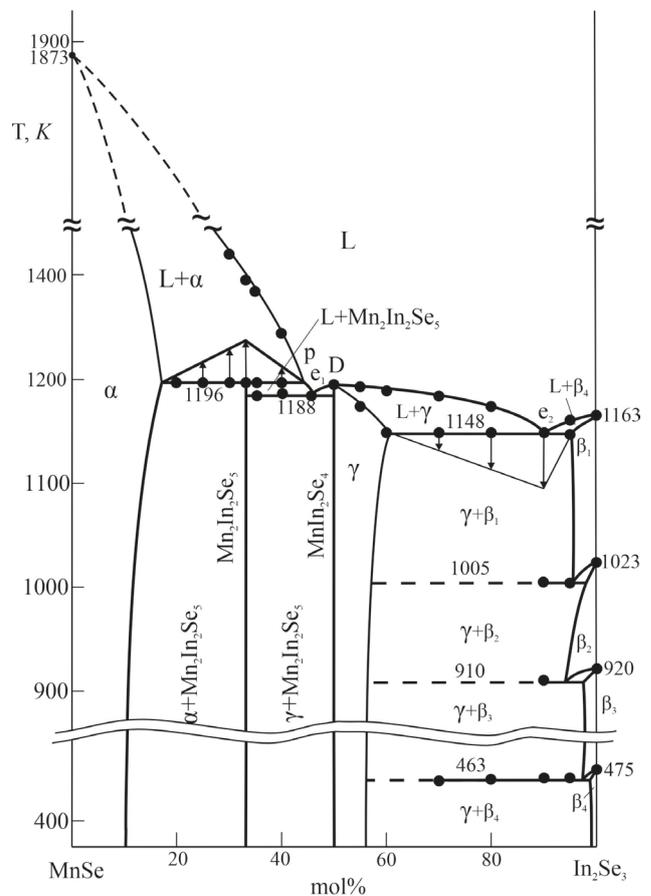


Fig. 5. Phase diagram of the MnSe–In₂Se₃ system

(γ -phase) towards an excess of the In₂Se₃. The second compound of the composition Mn₂In₂Se₅ melts with decomposition according to the peritectic reaction $L + \alpha \leftrightarrow \text{Mn}_2\text{In}_2\text{Se}_5$ at 1196 K. The peritectic point has a composition of 42 mol. % In₂Se₃, the γ -phase is in eutectic equilibrium with the neighboring phases:



(point e_1 , 45 mol. % In₂Se₃, 1188 K)

$L \leftrightarrow \beta_1 + \gamma$ (point e_2 , 90 mol. % In₂Se₃, 1148 K).

The compositions of the peritectic and eutectic points, as well as the homogeneity regions of the phases, were refined by the plotting of the Tamman's triangle (Fig. 5). It has been established that the homogeneity region of the α -phase at the peritectic temperature is 15 mol. %, and at eutectic temperature e_2 homogeneity regions of γ - and β_1 -phases reach

10 and 5 mol. %, respectively. With a decreasing temperature of the homogeneity region the α - and γ -phases were somewhat narrowed and, according to X-ray diffraction data (Fig. 1), at room temperature, they were ~10 and 5 mol. %.

The phase compositions of the alloys, in particular the areas of phase homogeneity, were confirmed by SEM results (Fig. 6). As can be seen, the SEM images are in accordance with the phase diagram: the alloy with the composition 55 mol. % In₂Se₃, as well as the alloy with the stoichiometric composition MnIn₂Se₄ are single-phase, and the other three samples from different two-phase regions of the phase diagram are two-phase.

The obtained pattern of phase equilibria in the MnSe–In₂Se₃ system differed significantly from the data obtained in [51]. The phase diagram presented in [51] reflected only one ternary compound: MnIn₂Se₄ with congruent melting at ~1200 K. In

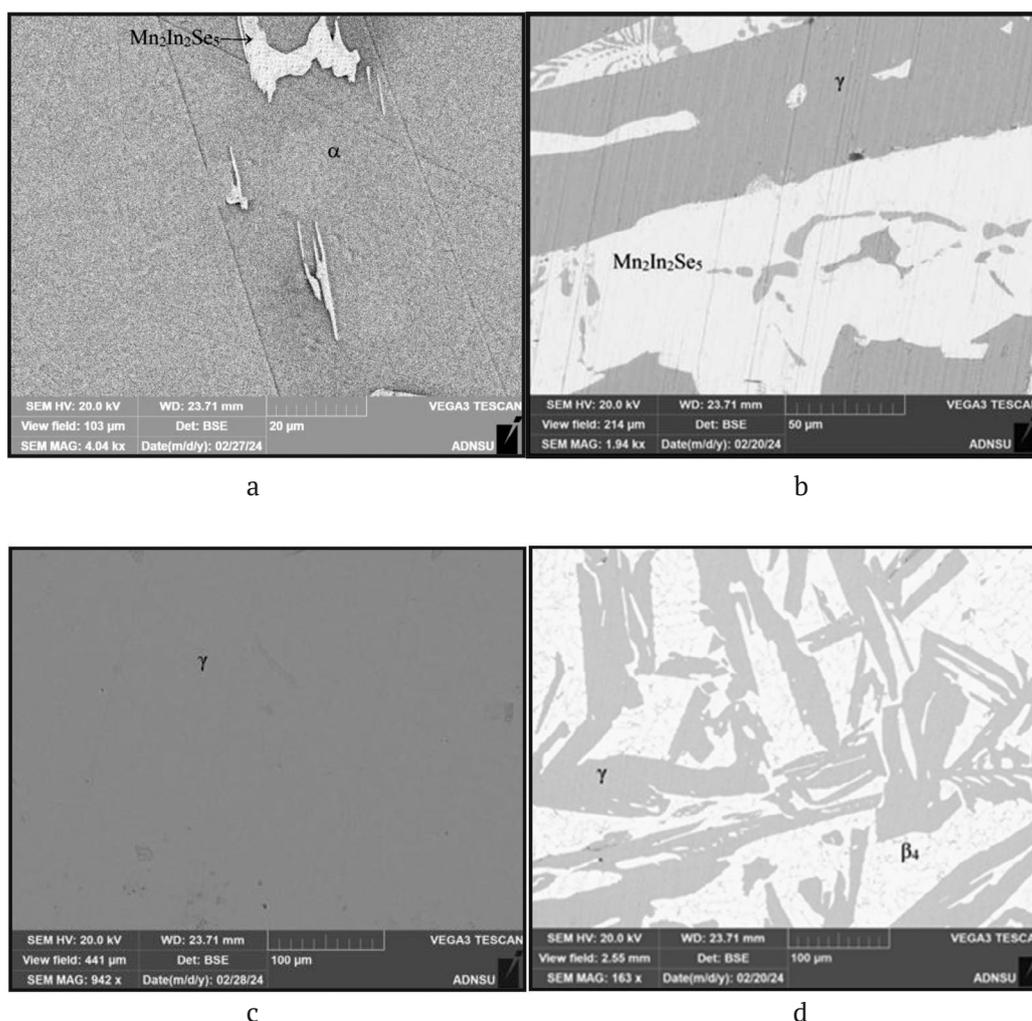


Fig. 6. SEM images of some single- and two-phase alloys of the MnSe–In₂Se₃ system: a) 15; b) 40; c) 55 and d) 70 mol. % In₂Se₃

addition, according to data [51], solubility based on MnSe was practically absent, and homogeneity regions based on various modifications of In₂Se₃ ranged from 5 (low temperature) to 25 mol. % (high temperature). Our data also differ significantly from data of [51] for the coordinates of eutectic and eutectoid equilibria.

4. Conclusions

Thus, we present a new refined version of the phase diagram of the MnSe–In₂Se₃ system, on which, in contrast to the data [51], in addition to MnIn₂Se₄, a ternary compound of the Mn₂In₂Se₅ composition, melting with decomposition according to a peritectic reaction at 1196 K, was also formed. According to our data, MnIn₂Se₄ melts congruently at 1193 K and is a phase of variable composition, the homogeneity region at room temperature is ~5 mol. %. The crystal structures and lattice parameters of the MnIn₂Se₄ and Mn₂In₂Se₅ compounds were refined based on the XRD data, using the Rietveld method. Both ternary compounds were shown to have a layered structure and crystallize in the $R\bar{3}m$ space group.

Author contributions

F. M. Mammadov – research concept, discussion of results, writing the article; S. Z. Imamaliyeva – processing of the obtained results and participation in writing the article; E. N. Ismailova – literature search and participation in experiments; I. R. Amiraslanov – conducting structural studies; E. I. Akhmedov – processing the obtained results and writing the article; M. B. Babanly – scientific leadership, scientific editing.

Conflict of interests

The authors declare that they have no known competing financial interests or personal relationships that could have influenced the work reported in this paper.

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